



IFW

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Ryoji HOSHI et al.

Group Art Unit: 1722

Application No.: 10/520,099

Examiner: F. HITESHEW

Filed: January 4, 2005

Docket No.: 122336

For: A SILICON WAFER FOR EPITAXIAL GROWTH, AN EPITAXIAL WAFER, AND A METHOD FOR PRODUCING IT

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In reply to the July 26, 2006 Office Action, please consider the following:

Amendments to the Claims as reflected in the listing of claims; and

Remarks.